





# JN Semiconductor®

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## 4A, 200V Ultrafast Diodes

The RURD420S is an ultrafast diode with soft recovery characteristics ( $t_{\rm rr}$  < 30ns). It has low forward voltage drop and has ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. It's low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits, reducing power loss in the switching transistors.

Formerly developmental type TA49034.

## Ordering Information

| PART NUMBER | PACKAGE | BRAND  |  |
|-------------|---------|--------|--|
| RURD420S    | TO-252  | RUR420 |  |

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-252 variant in tape and reel, i.e., RURD420S9A

### **Features**

| Ultrafast with Soft Recovery | <30ns              |
|------------------------------|--------------------|
| Operating Temperature        | 175 <sup>0</sup> C |
| Reverse Voltage              | 200V               |

- · Avalanche Energy Rated
- Planar Construction

## **Applications**

- Switching Power ج اام
- Power Switch. Cin as
- General rpose

## Fraka\_ing

PEDEC STYLE TO-252

CATHODE (FLANGE)

ENDESIGN

ATHCDL ANODE

## Symbol



**Absolute Max nu.** .atıı **S**  $T_C = 25^{\circ}C$ , Unless Ott erw se Specif et

|  | RURD420S   | UNITS |
|--|------------|-------|
| Peak F etitive /er Voltage                     | 200        | V     |
| Working ak Rev se Voltage                      | 200        | V     |
| DC Blockin, 'c' ge                             | 200        | V     |
| Average Recuired Fort /a: a Current            | 4          | Α     |
| $(T_C = 159^{\circ}C)$                         |            |       |
| Repetitive Poak Surge Current                  | 8          | Α     |
| (Square Wave, 20kHz)                           |            |       |
| Noncepatitive Peak Surge Curre co              | 40         | Α     |
| (Halfwave, 1 Phase, 60Hz)                      |            |       |
| Maximum Power Dissipation                      | 30         | W     |
| Avalanche Energy (See Figures 9 and 10)        | 10         | mJ    |
| Operating and Storage Temperature              | -65 to 175 | °С    |
| Maximum Lead Temperature for Soldering         |            |       |
| (Leads at 0.063 in. (1.6mm) from case for 10s) | 300        | оС    |
| Package Body for 10s, see Tech Brief 334       | 260        | οС    |

**Electrical Specifications**  $T_C = 25^{\circ}C$ , Unless Otherwise Specified

| SYMBOL         | TEST CONDITION   | MIN | TYP | MAX  | UNITS |
|----------------|--|-----|-----|------|-------|
| V <sub>F</sub> | I <sub>F</sub> = 4A                                      | -   | -   | 1.0  | V     |
|                | I <sub>F</sub> = 4A, T <sub>C</sub> = 150 <sup>o</sup> C | -   | -   | 0.83 | V     |

**Electrical Specifications**  $T_C = 25^{\circ}C$ , Unless Otherwise Specified

| SYMBOL          | TEST CONDITION                                     | MIN | TYP | MAX | UNITS |
|-----------------|--|-----|-----|-----|-------|
| I <sub>R</sub>  | V <sub>R</sub> = 200V                              | -   | -   | 100 | μА    |
|                 | $V_R = 200V, T_C = 150^{\circ}C$                   | -   | -   | 500 | μА    |
| t <sub>rr</sub> | I <sub>F</sub> = 1A, dI <sub>F</sub> /dt = 100A/μs | -   | -   | 30  | ns    |
|                 | $I_F = 4A$ , $dI_F/dt = 100A/\mu s$                | -   | -   | 35  | ns    |
| t <sub>a</sub>  | $I_F = 4A$ , $dI_F/dt = 100A/\mu s$                | -   | 11  | -   | ns    |
| t <sub>b</sub>  | $I_F = 4A$ , $dI_F/dt = 100A/\mu s$                | -   | 9   | -   | ns    |
| Q <sub>RR</sub> | $I_F = 4A$ , $dI_F/dt = 100A/\mu s$                | -   | 12  | -   | nC    |
| СЛ              | V <sub>R</sub> = 10V, I <sub>F</sub> = 0A          | -   | 15  | -   | pF    |
| $R_{	heta JC}$  |  | -   | -   | 5   | (C/V) |

#### **DEFINITIONS**

 $V_F$  = Instantaneous forward voltage (pw = 300 $\mu$ s, D = 2%).

I<sub>R</sub> = Instantaneous reverse current.

 $t_{rr}$  = Reverse recovery time (See Figure 8), summation of  $t_a$  +  $t_b$ .

t<sub>a</sub> = Time to reach peak reverse current (See Figure 8).

tb = Time from peak IRM to projected zero crossing of IRM based a st. aht a from peak IRM through 25% of IRM (See Figure 8).

Q<sub>RR</sub> = Reverse recovery charge.

 $C_J$  = Junction capacitance.

 $R_{\theta,JC}$  = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

## Typical Performance ;urves

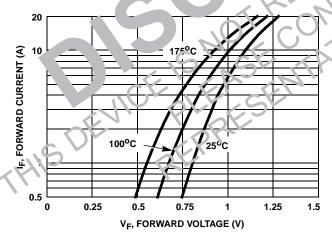


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

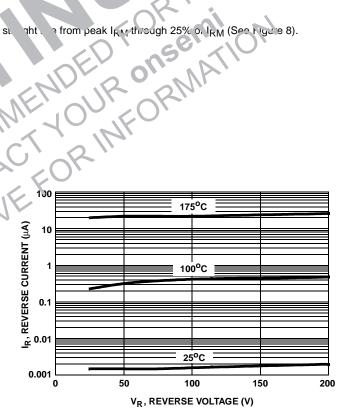


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

## Typical Performance Curves (Continued)

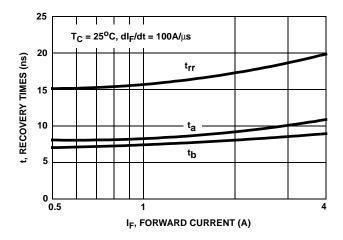


FIGURE 3. t<sub>rr</sub>, t<sub>a</sub> AND t<sub>b</sub> CURVES vs FORWARD CURRENT

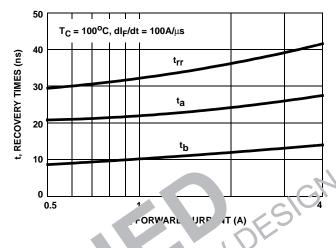
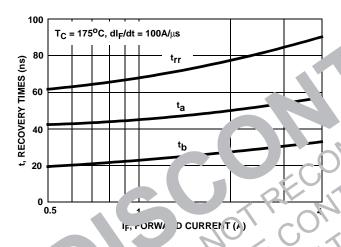


FIGURE 4 t<sub>rr</sub>, t<sub>a</sub> ND CUF \_S vs FORWARD CURRENT



FIGU 75. trr, AN tb CURYES IS FORVARD CURRENT

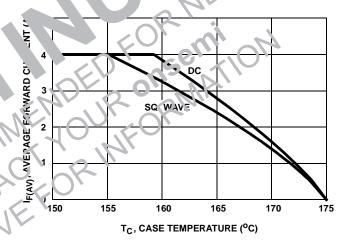


FIGURE 6. CURRENT DERATING CURVE

## Test Circuits and Waveforms

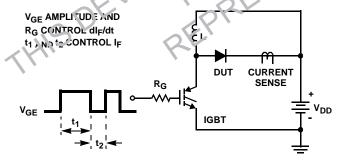


FIGURE 7.  $t_{rr}$  TEST CIRCUIT

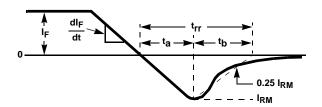


FIGURE 8.  $t_{rr}$  WAVEFORMS AND DEFINITIONS

## Test Circuits and Waveforms (Continued)

I = 1A L = 20mH  $R < 0.1\Omega$   $E_{AVL} = 1/2LI^2 \left[ V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right]$   $Q_1 = IGBT \left( BV_{CES} > DUT \ V_{R(AVL)} \right)$  L R CURRENT + O  $SENSE V_{DD}$   $V_{DD}$  OUT - O

FIGURE 9. AVALANCHE ENERGY TEST CIRCUIT

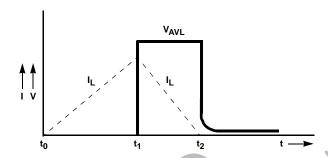


FIGURE 10. AVALANCHE CUP LENT > VOLTAGE WAVEFORMS

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| CROSSVOLT™                        | FRFET™                         | MicroPak™     | QS <sup>TM</sup>    | SyncFET™               |
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Stealth<sup>1</sup>

### ... YUC STA DEFINITIONS

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| P_asheer Identification  | Product Status            | Definition  |
|--------------------------|---------------------------|---|
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